2SD1436(K)

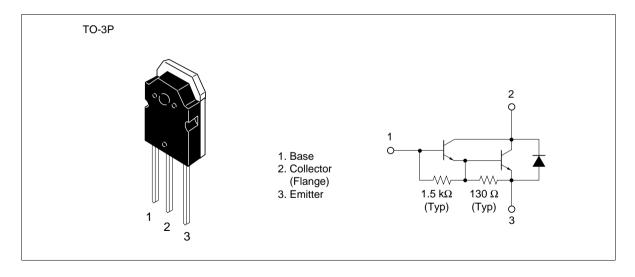
Silicon NPN Triple Diffused

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Application

Power switching complementary pair with 2SB1032(K)

Outline





2SD1436(K)

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

ltem	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	120	V
Collector to emitter voltage	V _{CEO}	120	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	Ι _c	10	А
Collector peak current	Г _{С (реак)}	15	А
Collector power dissipation	P _c * ¹	80	W
Junction temperature	Tj	150	٥C
Storage temperature	Tstg	-55 to +150	°C

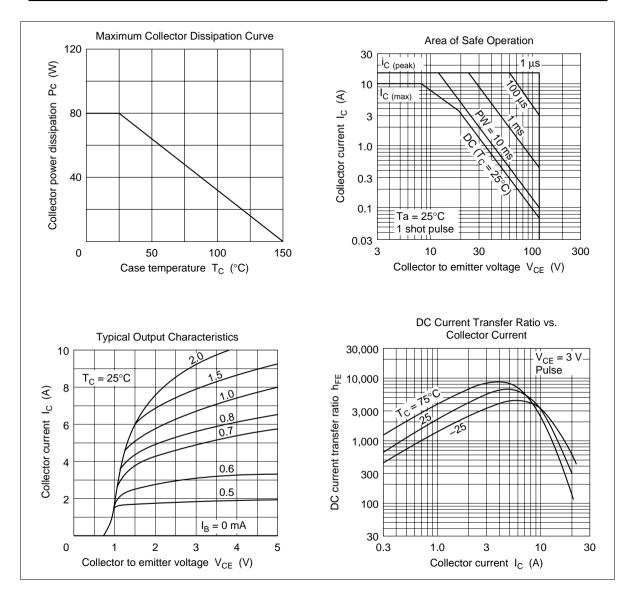
Note: 1. Value at $T_c = 25^{\circ}C$.

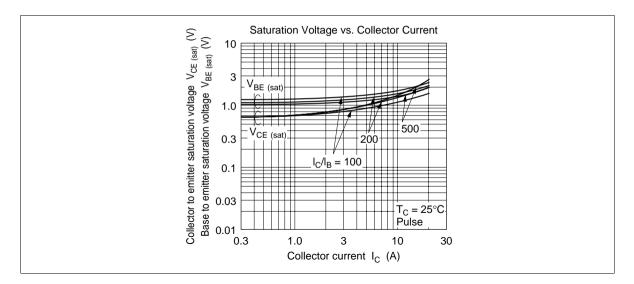
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	120	_	_	V	$I_{\rm C}$ = 25 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	_	V	$I_{\rm E} = 200$ mA, $I_{\rm C} = 0$
Collector cutoff current	I _{CBO}		—	100	μΑ	$V_{CB} = 120 \text{ V}, \text{ I}_{E} = 0$
	I _{CEO}	_	—	10	μA	V_{ce} = 100 V, R_{be} = ∞
DC current transfer ratio	h _{FE}	1000	—	20000		$V_{ce} = 3 \text{ V}, \text{ I}_{c} = 5 \text{ A}^{*1}$
Collector to emitter saturation	$V_{\text{CE (sat)1}}$	—	—	1.5	V	$I_{\rm c} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{CE (sat)2}	—	—	3.0	V	$I_{\rm C} = 10 \text{ A}, I_{\rm B} = 0.1 \text{ A}^{*1}$
Base to emitter saturation	$V_{\text{BE (sat)1}}$	—	—	2.0	V	$I_{\rm c} = 5 \text{ A}, I_{\rm B} = 10 \text{ mA}^{*1}$
voltage	V _{BE (sat)2}	_	_	3.5	V	$I_{\rm c} = 10$ A, $I_{\rm B} = 0.1$ A ^{*1}
Turn on time	Ton	_	0.8	_	μs	$I_{\rm C} = 5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = 10 \text{ mA}$
Turn off time	Toff	_	4.0	_	μs	

Note: 1. Pulse test.

2SD1436(K)

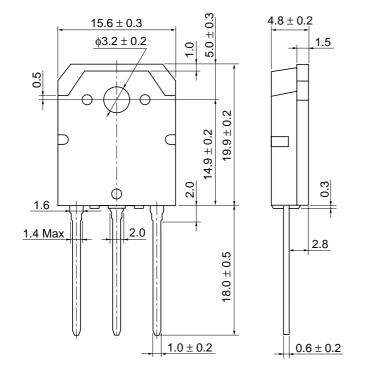


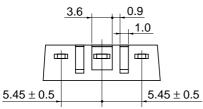


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Unit: mm

°O,





Hitachi Code	TO-3P
JEDEC	_
EIAJ	Conforms
Weight (reference value)	5.0 g

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